

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,196,003 B2
APPLICATION NO. : 10/774496
DATED : March 27, 2007
INVENTOR(S) : Yoshihisa Iba

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On Claims

Please delete the paragraphs beginning at column 6, line 64 and column 7, line 1, and insert the following paragraph.

--The etching of SiO₂ film 6 is performed using the plasma etching device, for example, under the condition of 20 sccm of C₄F₆, 15 sccm of O₂, 200 sccm of Ar, 4.00 Pa (30 mTorr) of pressure, and 1500 W of RF source power.--

Signed and Sealed this

Fifteenth Day of April, 2008

A handwritten signature in black ink, reading "Jon W. Dudas". The signature is stylized, with a large loop for the "J" and a cursive "Dudas".

JON W. DUDAS
Director of the United States Patent and Trademark Office